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(54) Title: FORMATION OF SILICON OXIDE USING NON-CARBON FLOWABLE CVD PROCESSES

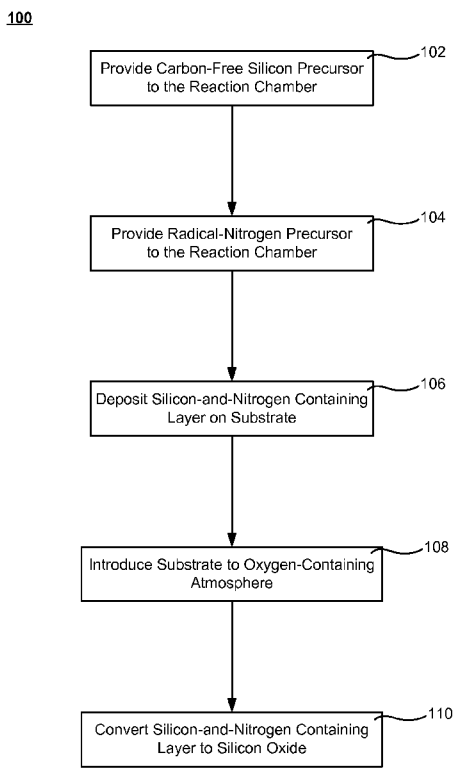


FIG. 1

(57) Abstract: A method of forming a silicon oxide layer is described. The method may include the steps of mixing a carbon-free silicon-and-nitrogen containing precursor with a radical precursor, and depositing a silicon-and-nitrogen containing layer on a substrate. The silicon-and-nitrogen containing layer is then converted to the silicon oxide layer.

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